

EUROPEAN PATENT OFFICE

EXPRESS MAIL No. EL615231713US

Patent Abstracts of Japan

PUBLICATION NUMBER : 08255791
 PUBLICATION DATE : 01-10-96

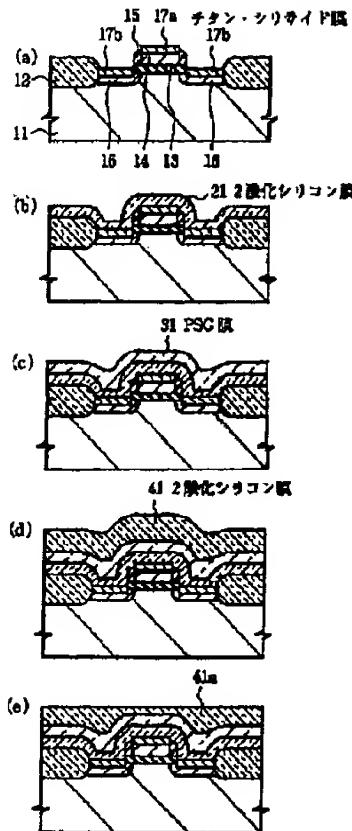
APPLICATION DATE : 17-03-95
 APPLICATION NUMBER : 07057849

APPLICANT : NEC CORP;

INVENTOR : KOYANAGI KENICHI;

INT.CL. : H01L 21/316 H01L 21/304 H01L 21/324
 H01L 21/768

TITLE : FORMATION OF INTERLAYER
 INSULATING FILM OF
 SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To form an interlayer insulating film covering a MOS transistor of a titanium salicide structure by suppressing degradation of transistor characteristics and coagulation of titanium silicide film.

CONSTITUTION: A silicon dioxide film 21 is formed by the LPCVD process, a PSG film 31 is formed by the APCVD process using ozone, TEOS, etc., as raw materials, these films are heat-treated in a 750°C nitrogen atmosphere, and a silicon dioxide film 41 is formed by the ECR-PECVD process, and the surface of this silicon dioxide film 41 is polished by the CMP process.

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